INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(PTO-1449)

OIPE JC173 MAR 22 2001 PATENT & TRADEMARK OFFICE

ATTY. DOCKET NO.	SERIAL NO.,
50275-0014	**09/675,197**

APPLICANT
Christophe Pierrat, et al.

FILING DATE	GROUP
September 29, 2000	~~2842~~ 2823

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	4,812,962	03/14/89	Witt			
	5,051,598	09/24/91	Ashton, et al.			
	5,182,718	01/26/93	Harafugi, et al.			
	5,241,185	08/31/93	Meiri, et al.			
	5,242,770	09/07/93	Chen, et al.			
	5,256,505	10/26/93	Chen, et al.			
	5,316,878	05/31/94	Saito, et al.			
	5,326,659	07/05/94	Liu, et al.			

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No
	WO 00/67074	11/09/00	PCT				

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EXAMINER	DATE CONSIDERED
	3/20/04

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OIPE JC17a MAR 22 2001 PATENT & TRADEMARK OFFICE

ATTY. DOCKET NO.	SERIAL NO.,
50275-0014	09/675,197

APPLICANT: Christophe Pierrat, et al.

FILING DATE	GROUP
September 29, 2000	~~2812~~ 2825

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	5,340,700	08/23/94	Chen, et al.			
	5,424,154	06/13/95	Borodovsky			
	5,432,714	07/11/95	Chung, et al.			
	5,447,810	09/05/95	Chen, et al.			
	5,533,148	06/02/96	Sayah, et al.			
	5,538,815	07/23/96	Oi, et al.			
	5,553,273	09/03/96	Liebmann			
	5,572,598	11/05/96	Wihl, et al.			

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

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(PTO-1449)

OIPE JC173 MAR 2 2 2001 PATENT & TRADEMARK OFFICE

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50275-0014	09/675,197
APPLICANT: Christophe Pierrat, et al.	
FILING DATE: September 29, 2000	GROUP: ~~2812~~ 2825

U.S. PATENT DOCUMENTS

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	5,663,893	09/02/97	Wampler, et al.			
	5,702,848	12/30/97	Spence			
	5,705,301	01/06/98	Garza, et al.			
	5,707,765	01/13/98	Chen			
	5,740,068	04/14/98	Liebmann, et al.			
	5,795,688	08/18/98	Burdorf, et al.			

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No
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	3/1/04

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OIPE JC173 MAR 22 2001 PATENT & TRADEMARK OFFICE

ATTY. DOCKET NO.	SERIAL NO.,
50275-0014	**09/675,197**

APPLICANT: **Christophe Pierrat, et al.**

FILING DATE	GROUP
September 29, 2000	~~2842~~ 2825

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
W	5,801,954	09/01/98	Le, et al.			
	5,804,340	09/08/98	Garza, et al.			
	5,815,685	09/29/98	Kamon			
	5,825,647	10/20/98	Tsudaka			
	5,827,623	10/27/98	Ishida, et al.			
	5,847,959	12/08/98	Veneklasen, et al.			
	5,849,440	12/15/98	Lucas, et al.			
	5,863,682	01/26/99	Abe, et al.			
	6,081,658	06/27/00	Rieger, et al.			

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No

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	3/2007

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50275-0014	09/675,197
APPLICANT: Christophe Pierrat, et al.	
FILING DATE: September 29, 2000	GROUP: ~~2812~~ 2825

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER	DATE CONSIDERED
	5/2007

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant

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INFORMATION DISCLOSURE CITATION PTO-1449	ATTY. DOCKET NO. NTI-019-2	SERIAL NO. 09/675,197
	APPLICANT Pierrat, et al.	
	FILING DATE 9/29/00	GROUP ~~2812~~ 2825

OIPE JC54 OCT 15 2001 PATENT & TRADEMARK OFFICE

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
WP	4,231,811	11/4/80	Somekh, et al.	148	1.5	9/13/79
	4,456,371	6/26/84	Lin	355	71	6/30/82
	4,902,899	2/20/90	Lin, et al.	250	492.1	6/1/87
	5,498,579	3/12/96	Borodovsky, et al.	437	250	6/8/94
	5,553,274	9/3/96	Liebmann	395	500	6/6/95
	5,636,002	6/3/97	Garofalo	355	53	10/31/95
	5,663,017	9/2/97	Schinella, et al.	430	5	6/7/95
	5,663,893	9/2/97	Wampler et al.	364	491	5/3/95
	5,723,233	3/3/98	Garza, et al.	430	5	2/27/96
	5,766,806	6/16/98	Spence	430	5	9/9/96
	5,821,014	10/13/98	Chen, et al.	430	5	2/28/97
	5,862,058	1/19/99	Samuels, et al.	364	491	5/16/96
	5,879,844	3/9/99	Yamamoto, et al.	430	30	12/20/96
	5,885,734	3/23/99	Pierrat, et al.	430	5	8/15/96
	5,900,338	5/4/99	Garza, et al.	430	5	8/15/97
	5,994,002	11/30/99	Matsuoka	430	5	9/4/97
	6,004,702	12/21/99	Lin	430	5	5/21/98
	6,077,310	6/20/00	Yamamoto, et al.	716	19	1/29/99
	6,078,738	6/20/00	Garza, et al.	395	500.22	5/8/97

EXAMINER [signature] DATE CONSIDERED 3/2004

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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
WM	3-210560	9/13/91	JP - ABSTRACT			☑	☐
	8-236317	9/6/96	JP - ABSTRACT			☑	☐
	10-133356	5/22/98	JP - ABSTRACT			☑	☐
	11-143085	5/28/99	JP - ABSTRACT			☑	☐
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	FILING DATE 9/29/00	GROUP ~~2812~~ 2825

OIPE JC54 OCT 15 2001 PATENT & TRADEMARK OFFICE

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OCT 15 2001
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USA

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	Applicant PIERRAT, Christophe	
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OIPE JC149 APR 15 2002 PATENT & TRADEMARK OFFICE

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
W	4,426,584	1/17/1984	Bohlen, et al.	250	492.2	6/3/1981
	4,895,780	1/23/1990	Nissan-Cohen, et al.	430	5	10/25/1988
	5,208,124	5/4/1993	Sporon-Fiedler, et al.	430	5	3/19/1991
	5,682,323	10/28/1997	Pasch, et al.	364	491	3/6/1995
	5,958,635	9/28/1999	Reich, et al.	430	30	10/20/1997
	5,972,541	10/26/1999	Sugasawara, et al.	430	5	3/4/1998
	6,007,310	12/28/1999	Jacobsen, et al.	417	362	5/23/1997
	6,114,071	9/5/2000	Chen, et al.	430	5	4/6/1998
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	Applicant: PIERRAT, Christophe	
	Filing Date: 9/29/2000	Group: 2825 ~~2812~~

OIPE JC149 APR 15 2002 PATENT & TRADEMARK OFFICE

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
VM	3-80525	4/5/1991	JP - ABSTRACT			☑	☐
	2,324,169 A	10/14/1998	GB			☐	☐
	WO 99/47981	9/23/1999	WO			☐	☐

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PTO-1449

Atty. Docket No.	Serial No.
NTI-019-2	09/675,197

Applicant
PIERRAT, Christophe

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	Applicant PIERRAT, Christophe	
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